- State-of-the-Art EPIC-IIB ${ }^{\text {TM }}$ BiCMOS Design Significantly Reduces Power Dissipation
- ESD Protection Exceeds 2000 V Per MIL-STD-883C, Method 3015; Exceeds 200 V Using Machine Model ( $\mathrm{C}=200 \mathrm{pF}$, $R=0$ )
- Latch-Up Performance Exceeds 500 mA Per JEDEC Standard JESD-17
- Typical V at $\mathrm{V}_{\mathrm{CC}}=5 \mathrm{~V}, \mathrm{~T}_{\mathrm{A}}=25^{\circ} \mathrm{C}$
- High-Drive Outputs (-32-mA IOH, 64-mA IOL)
- Multiplexed Real-Time and Stored Data
- Inverting Data Paths
- Package Options Include Plastic Small-Outline Packages (DW), Ceramic Chip Carriers (FK), and Standard Plastic and Ceramic 300-mil DIPs (JT, NT)


## description

These devices consist of bus transceiver circuits, D-type flip-flops, and control circuitry arranged for multiplexed transmission of data directly from the input bus or from the internal registers. Data on the A or B bus is clocked into the registers on the low-to-high transition of the appropriate clock (CLKAB or CLKBA) input. Figure 1 illustrates the four fundamental bus-management functions that can be performed with the 'ABT648.
Output-enable ( $\overline{\mathrm{OE}}$ ) and direction-control (DIR) inputs are provided to control the transceiver functions. In the transceiver mode, data present at the high-impedance port may be stored in either register or in both.


The select-control (SAB and SBA) inputs can multiplex stored and real-time (transparent mode) data. The direction control (DIR) determines which bus will receive data when $\overline{\mathrm{OE}}$ is low. In the isolation mode ( $\overline{\mathrm{OE}}$ high), A data may be stored in one register and/or B data may be stored in the other register.
When an output function is disabled, the input function is still enabled and may be used to store and transmit data. Only one of the two buses, A or B, may be driven at a time.

To ensure the high-impedance state during power up or power down, $\overline{\mathrm{OE}}$ should be tied to $\mathrm{V}_{\mathrm{Cc}}$ through a pullup resistor; the minimum value of the resistor is determined by the current-sinking capability of the driver.
The SN54ABT648 is characterized for operation over the full military temperature range of $-55^{\circ} \mathrm{C}$ to $125^{\circ} \mathrm{C}$. The SN74ABT648 is characterized for operation from $-40^{\circ} \mathrm{C}$ to $85^{\circ} \mathrm{C}$.


Figure 1. Bus-Management Functions
Pin numbers shown are for DW, JT, and NT packages.

FUNCTION TABLE

| INPUTS |  |  |  |  |  | DATA I/O |  | OPERATION OR FUNCTION |
| :---: | :---: | :---: | :---: | :---: | :---: | :---: | :---: | :---: |
| $\overline{\mathrm{OE}}$ | DIR | CLKAB | CLKBA | SAB | SBA | A1 THRU A8 | B1 THRU B8 |  |
| X | X | $\uparrow$ | X | X | X | Input | Unspecified $\dagger$ | Store A, B unspecified $\dagger$ |
| X | X | X | $\uparrow$ | X | X | Unspecified $\dagger$ | Input | Store B, A unspecified $\dagger$ |
| H | X | $\uparrow$ | $\uparrow$ | X | X | Input | Input | Store A and B data |
| H | X | H or L | H or L | X | X | Input | Input | Isolation, hold storage |
| L | L | X | X | X | L | Output | Input | Real-time $\bar{B}$ data to $A$ Bus |
| L | L | X | H or L | X | H | Output | Input | Stored $\overline{\mathrm{B}}$ data to A Bus |
| L | H | X | X | L | X | Input | Output | Real-time $\bar{A}$ data to B Bus |
| L | H | H or L | X | H | X | Input | Output | Stored $\overline{\mathrm{A}}$ data to B Bus |

$\dagger$ The data output functions may be enabled or disabled by various signals at the $\overline{\mathrm{OE}}$ and DIR inputs. Data input functions are always enabled; i.e., data at the bus pins will be stored on every low-to-high transition of the clock inputs.

## logic symbol $\ddagger$


$\ddagger$ This symbol is in accordance with ANSI/IEEE Std 91-1984 and IEC Publication 617-12.
Pin numbers shown are for the DW, JT, and NT packages.
logic diagram (positive logic)


Pin numbers shown are for DW, JT, and NT packages.
absolute maximum ratings over operating free－air temperature range（unless otherwise noted）$\dagger$

| Supply voltage range， $\mathrm{V}_{\mathrm{CC}}$ | －0．5 V to 7 V |
| :---: | :---: |
| Input voltage range， $\mathrm{V}_{\mathrm{I}}$（except I／O ports）（see Note 1） | －0．5 V to 7 V |
| Voltage range applied to any output in the high state or power－off sta | －0．5 V to 5．5 V |
| Current into any output in the low state， $\mathrm{I}_{0}$ ：SN54ABT648 | 96 mA |
| SN74ABT648 | 128 mA |
| Input clamp current， $\mathrm{I}_{\mathrm{IK}}\left(\mathrm{V}_{\mathrm{l}}<0\right)$ | －18 mA |
| Output clamp current， $\mathrm{l}_{\mathrm{OK}}\left(\mathrm{V}_{\mathrm{O}}<0\right)$ | －50 mA |
| Maximum power dissipation at $\mathrm{T}_{\mathrm{A}}=55^{\circ} \mathrm{C}$（in still air）： $\begin{aligned} & \text { DW package } \\ & \text { NT package }\end{aligned}$ | ．．．1 W |
| Storage temperature range | $-65^{\circ} \mathrm{C}$ to $150^{\circ} \mathrm{C}$ |

$\dagger$ Stresses beyond those listed under＂absolute maximum ratings＂may cause permanent damage to the device．These are stress ratings only，and functional operation of the device at these or any other conditions beyond those indicated under＂recommended operating conditions＂is not implied．Exposure to absolute－maximum－rated conditions for extended periods may affect device reliability．
NOTE 1：The input and output negative－voltage ratings may be exceeded if the input and output clamp－current ratings are observed．
recommended operating conditions（see Note 2）

|  |  | SN54ABT648 |  | SN74ABT648 |  | UNIT |
| :---: | :---: | :---: | :---: | :---: | :---: | :---: |
|  |  | MIN | MAX | MIN | MAX |  |
| $\mathrm{V}_{\mathrm{CC}}$ | Supply voltage | 4.5 | 5.5 | 4.5 | 5.5 | V |
| $\mathrm{V}_{\text {IH }}$ | High－level input voltage | 2 |  | 2 |  | V |
| $\mathrm{V}_{\text {IL }}$ | Low－level input voltage |  | 0.8 |  | 0.8 | V |
| $\mathrm{V}_{1}$ | Input voltage | 0 | $\mathrm{V}_{\mathrm{CC}}$ | 0 | $\mathrm{V}_{\mathrm{CC}}$ | V |
| ${ }^{\mathrm{IOH}}$ | High－level output current |  | －24 |  | －32 | mA |
| l OL | Low－level output current |  | 48 |  | 64 | mA |
| $\Delta t / \Delta v$ | Input transition rise or fall rate |  | 5 |  | 5 | ns／V |
| $\mathrm{T}_{\mathrm{A}}$ | Operating free－air temperature | －55 | 125 | －40 | 85 | ${ }^{\circ} \mathrm{C}$ |

NOTE 2：Unused or floating pins（input or I／O）must be held high or low．

SN54ABT648, SN74ABT648

## electrical characteristics over recommended operating free-air temperature range (unless otherwise noted)


$\dagger$ All typical values are at $\mathrm{V}_{\mathrm{CC}}=5 \mathrm{~V}$.
$\ddagger$ On products compliant to MIL-STD-883, Class B, this parameter does not apply.
§ The parameters IOZH and IOZL include the input leakage current.
I Not more than one output should be tested at a time, and the duration of the test should not exceed one second.
\# This is the increase in supply current for each input that is at the specified TTL voltage level rather than $V_{C C}$ or GND.
timing requirements over recommended ranges of supply voltage and operating free-air temperature (unless otherwise noted)

|  |  |  | $\begin{aligned} & \mathrm{V}_{\mathrm{CC}} \\ & \mathrm{~T}_{\mathrm{A}}= \end{aligned}$ | $5 \mathrm{~V},$ | SN54 | T648 | SN74A | T648 | UNIT |
| :---: | :---: | :---: | :---: | :---: | :---: | :---: | :---: | :---: | :---: |
|  |  |  | MIN | MAX | MIN | MAX | MIN | MAX |  |
| ${ }^{\text {f clock }}$ | Clock frequency |  |  |  |  |  |  |  | MHz |
| $\mathrm{t}_{\mathrm{w}}$ | Pulse duration, CLK high or low |  |  |  |  |  |  |  | ns |
|  | Setup time, A or B before CLKAB $\uparrow$ or CLKBA $\uparrow$ | High |  |  |  |  |  |  | ns |
|  |  | Low |  |  |  |  |  |  |  |
| th | Hold time, A or B after CLKAB $\uparrow$ or CLKBA $\uparrow$ |  |  |  |  |  |  |  | ns |

switching characteristics over recommended ranges of supply voltage and operating free-air temperature, $\mathrm{C}_{\mathrm{L}}=50 \mathrm{pF}$ (unless otherwise noted) (see Figure 2)

| PARAMETER | FROM (INPUT) | TO (OUTPUT) | $\begin{aligned} & \mathrm{V}_{\mathrm{CC}}=5 \mathrm{~V}, \\ & \mathrm{~T}_{\mathrm{A}}=25^{\circ} \mathrm{C} \end{aligned}$ |  |  | SN54ABT648 |  | SN74ABT648 |  | UNIT |
| :---: | :---: | :---: | :---: | :---: | :---: | :---: | :---: | :---: | :---: | :---: |
|  |  |  | MIN | TYP | MAX | MIN | MAX | MIN | MAX |  |
| $f_{\text {max }}$ |  |  |  |  |  |  |  |  |  | MHz |
| tPLH | $A$ or $B$ | B or A |  |  |  |  |  |  |  | ns |
| tPHL |  |  |  |  |  |  |  |  |  |  |
| tPLH | CLKBA or CLKAB | A or B |  |  |  |  |  |  |  | ns |
| tPHL |  |  |  |  |  |  |  |  |  |  |
| tPLH | SBA or SABT (with A or B high) | A or B |  |  |  |  |  |  |  | ns |
| tPHL |  |  |  |  |  |  |  |  |  |  |
| tPLH | SBA or SABT (with A or B low) | $A$ or B |  |  |  |  |  |  |  | ns |
| tPHL |  |  |  |  |  |  |  |  |  |  |
| tPZH | $\overline{\text { OEBA }}$ | A or B |  |  |  |  |  |  |  | ns |
| tPZL |  |  |  |  |  |  |  |  |  |  |
| tPHZ | $\overline{\text { OEBA }}$ | A or B |  |  |  |  |  |  |  | ns |
| tPLZ |  |  |  |  |  |  |  |  |  |  |
| tPZH | DIR | A or B |  |  |  |  |  |  |  | ns |
| tPZL |  |  |  |  |  |  |  |  |  |  |
| tPHZ | DIR | A or B |  |  |  |  |  |  |  | ns |
| tplZ |  |  |  |  |  |  |  |  |  |  |

$\dagger$ These parameters are measured with the internal output state of the storage registers opposite to that of the bus input.

## PARAMETER MEASUREMENT INFORMATION



| TEST | S1 |
| :---: | :---: |
| $\mathbf{t}_{\text {PLH }} / \mathbf{t} \mathbf{P H L}$ | Open |
| $\mathbf{t P L Z}^{\prime} \mathbf{t} \mathbf{P Z L}$ | 7 V |
| $\mathbf{t}_{\mathbf{P H Z}} / \mathbf{t} \mathbf{P Z H}$ | Open |



Figure 2. Load Circuit and Voltage Waveforms

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